

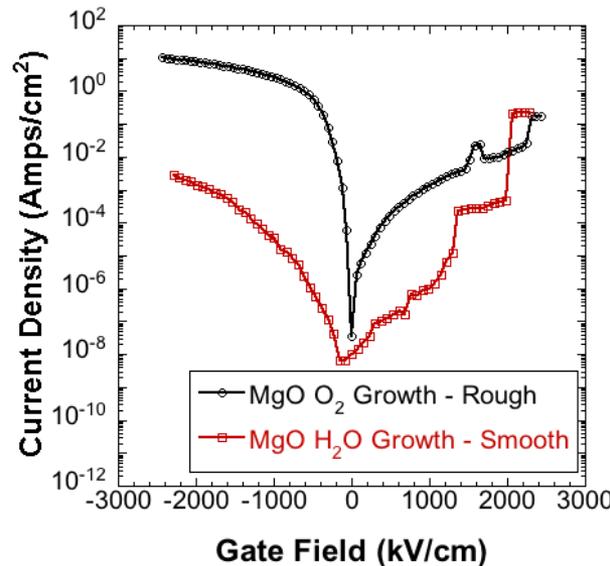
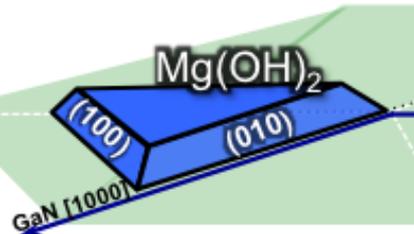
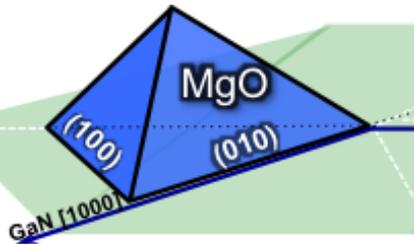
# Reliable High-Performance Gate Oxides for Wide Band Gap Devices

Jon Ihlefeld and Stan Atcitty, Sandia National Laboratories

jihlefe@sandia.gov, (505) 844-3162, satcitt@sandia.gov, (505) 284-2701

## Purpose

- Gate dielectrics are a key limiter in GaN- and SiC-based power electronics technology
- Engineered gates will enable the development of robust and reliable MOSFETs



## Impact

- Increased System Performance and Reliability
- Reduced System Cost
- Reduced Power Electronics Size